MM2102
1024 Bit Fully Decoded Static Random Access Memory

REFERENCE TABLE

Code	Stock No.
MM2102N	34856H

GENERAL DESCRIPTION

The MM2102 is a 1024 word by one bit static random access read write memory manufactured using N-channel enhancement mode silicon gate technology. Static storage cells eliminate the need for clocks and refresh. Data in and data out have the same polarity and the read operation is nondestructive.

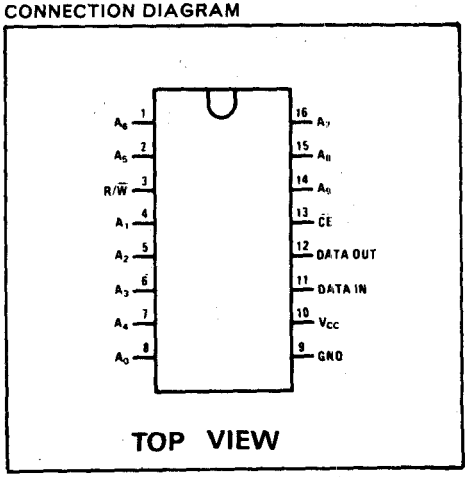
Low threshold silicon gate N-channel technology allows complete DTL/TTL compatibility of all inputs and outputs as well as a single +5V supply. The separate chip enable input (CE) controlling the TRI-STATE output allows easy memory expansion by OR-tying individual devices to a data bus.

The simple interface and high performance make the MM2102 ideally suited for those applications, for large and small storage capacity, where cost is an important design consideration.

ABSOLUTE MAXIMUM RATINGS

Voltage at any pin	−0.5V to +7.0V
Operating temperature range	0°C to 70°C
Storage temperature range	−65°C to +150°C
Power dissipation	1.0W
Lead temperature (soldering 10 sec)	300°C

CONNECTION DIAGRAM



TOP VIEW

See outline drawing No. 111 for dimensions.

FEATURES

Single +5.0V supply.
All inputs and output directly DTL/TTL compatible.
Static operation – no clocks or refreshing required.
Low power. 150mW typ.
High speed. 500ns typ.
TRI-STATE output for bus interface.
Chip enable allows simple memory expansion.
On chip address decode.
All inputs protected against static discharge.
Low cost 16-pin Epoxy B package.